

HiPerFAST™ IGBTs
C2-Class High Speed
w/ Diode

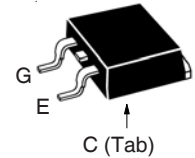
IXGA16N60C2D1
IXGP16N60C2D1
IXGH16N60C2D1

V_{CES} = 600V
I_{C110} = 16A
V_{CE(sat)} ≤ 3.0V
t_{fi(typ)} = 33ns

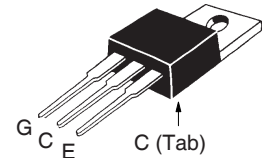


Symbol	Test Conditions	Maximum Ratings	
V _{CES}	T _J = 25°C to 150°C	600	V
V _{CGR}	T _J = 25°C to 150°C, R _{GE} = 1MΩ	600	V
V _{GES}	Continuous	±20	V
V _{GEM}	Transient	±30	V
I _{C25}	T _C = 25°C	40	A
I _{C110}	T _C = 110°C	16	A
I _{F110}	T _C = 110°C	11	A
I _{CM}	T _C = 25°C, 1ms	100	A
SSOA (RBSOA)	V _{GE} = 15V, T _J = 125°C, R _G = 22Ω Clamped Inductive load	I _{CM} = 32 V _{CE} ≤ V _{CES}	A
P _C	T _C = 25°C	150	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
M _d	Mounting Torque (TO-220 & TO-247)	1.13/10	Nm/lb.in.
F _C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
T _L	Maximum Lead Temperature for Soldering	300	°C
T _{SOLD}	1.6mm (0.062 in.) from Case for 10s	260	°C
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

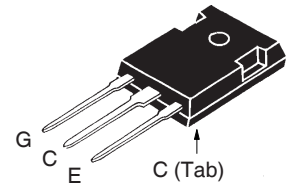
TO-263 AA (IXGA)



TO-220AB (IXGP)



TO-247 (IXGH)



G = Gate C = Collector
 E = Emitter Tab = Collector

Features

- Optimized for Low Switching Losses
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V _{GE(th)}	I _C = 250μA, V _{CE} = V _{GE}	3.0		5.5 V
I _{CES}	V _{CE} = V _{CES} , V _{GE} = 0V T _J = 125°C			25 μA 1 mA
I _{GES}	V _{CE} = 0V, V _{GE} = ±20V			±100 nA
V _{CE(sat)}	I _C = 12A, V _{GE} = 15V, Note1 T _J = 125°C		1.8	3.0 V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 12\text{A}, V_{CE} = 10\text{V}$, Note 1	8		S
C_{ies} C_{oes} C_{res}	} $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		657	pF
			72	pF
			22	pF
$Q_{g(on)}$ Q_{ge} Q_{gc}	} $I_C = 12\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		25	nC
			5	nC
			13	nC
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	} Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 12\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 22\Omega$ Note 2		16	ns
			17	ns
			0.16	mJ
			75	ns
			33	ns
			0.09	0.16 mJ
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	} Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 12\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 22\Omega$ Note 2		16	ns
			18	ns
			0.27	mJ
			115	ns
			100	ns
			0.27	mJ
R_{thJC} R_{thCK}	TO-220 TO-247		0.83	$^\circ\text{C/W}$
		0.50	$^\circ\text{C/W}$	
		0.21	$^\circ\text{C/W}$	

Reverse Diode (FRED)

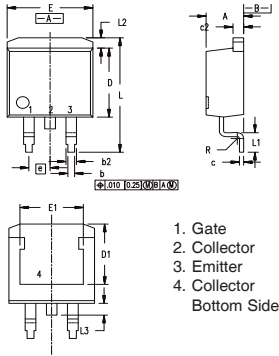
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 10\text{A}, V_{GE} = 0\text{V}$, Note 1 $T_J = 125^\circ\text{C}$		1.7	3.0 V V
I_{RM} t_{rr} t_{rr}	} $I_F = 12\text{A}, V_{GE} = 0\text{V}$, $-di_F/dt = 100\text{A}/\mu\text{s}, V_R = 100\text{V}, T_J = 125^\circ\text{C}$		2.5	A
			110	ns
	$I_F = 1\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}, V_R = 30\text{V}$		30	ns
R_{thJC}				2.5 $^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{Clamp})$, T_J or R_G .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

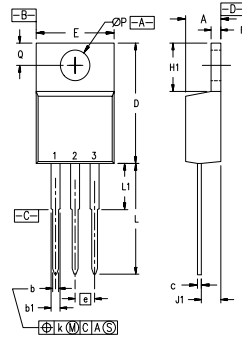
TO-263 (IXGA) Outline



- 1. Gate
 - 2. Collector
 - 3. Emitter
 - 4. Collector
- Bottom Side

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.40	0.74	.016	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.280	.320
E	9.65	10.41	.380	.405
E1	6.22	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.13	0	.005

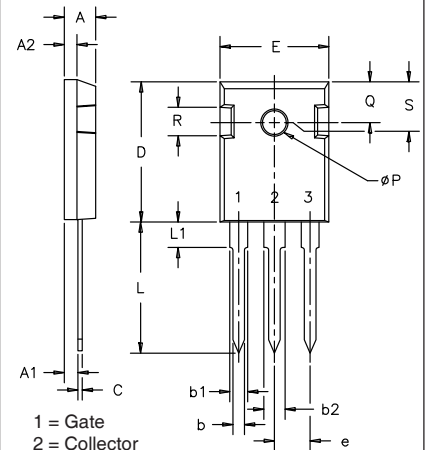
TO-220 (IXGP) Outline



- Pins: 1 - Gate 2 - Collector
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

TO-247 (IXGH) AD Outline



- 1 = Gate
2 = Collector
3 = Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A1	.087	.102	2.2	2.54
A2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b1	.065	.084	1.65	2.13
b2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
ØP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

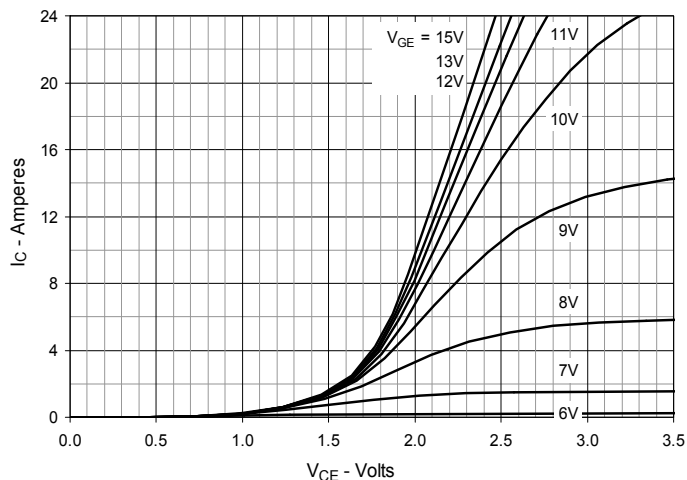


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

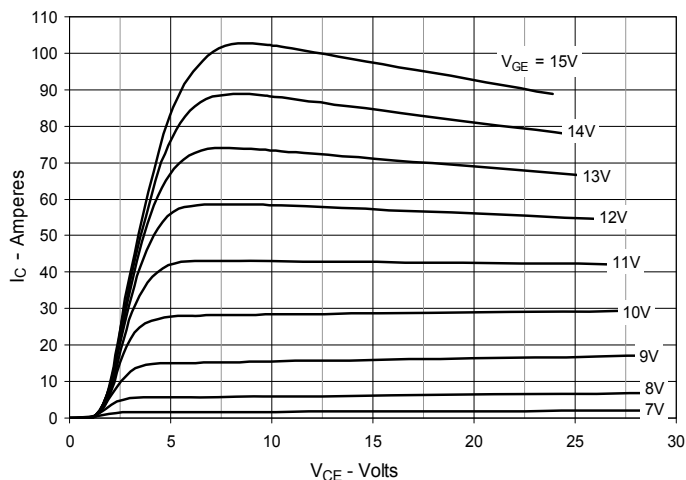


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

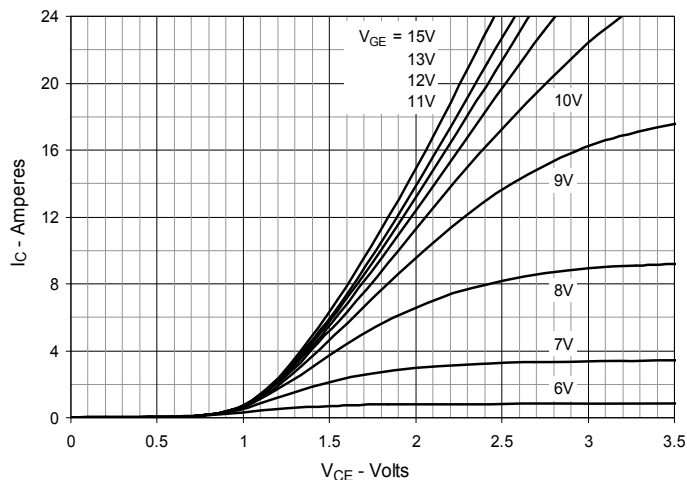


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

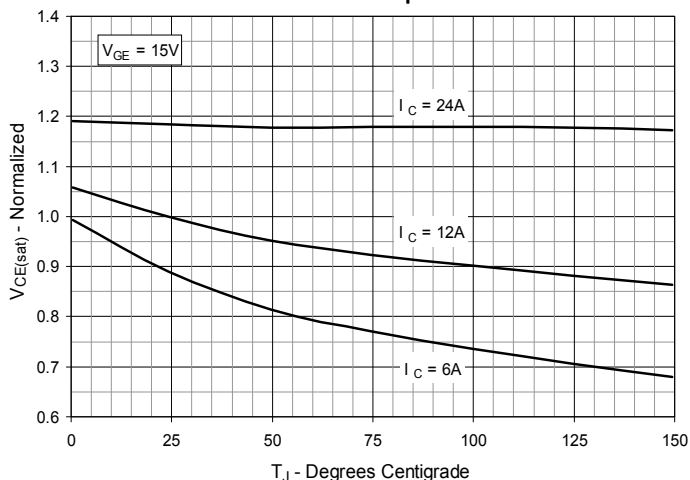


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

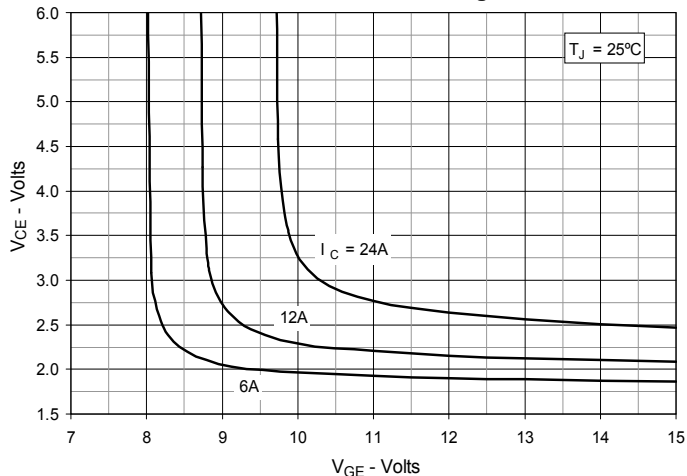


Fig. 6. Input Admittance

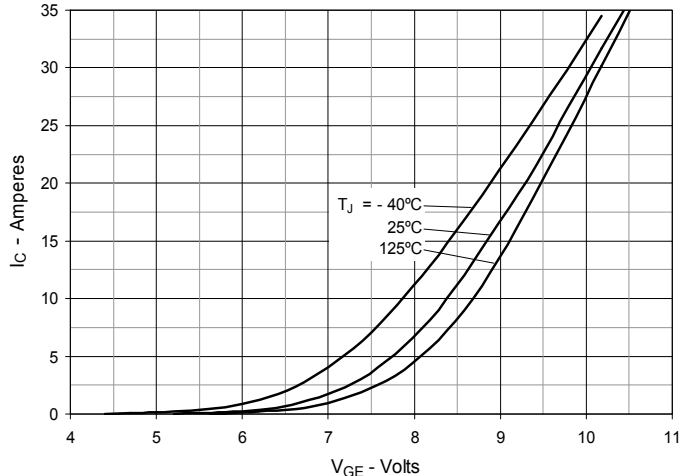


Fig. 7. Transconductance

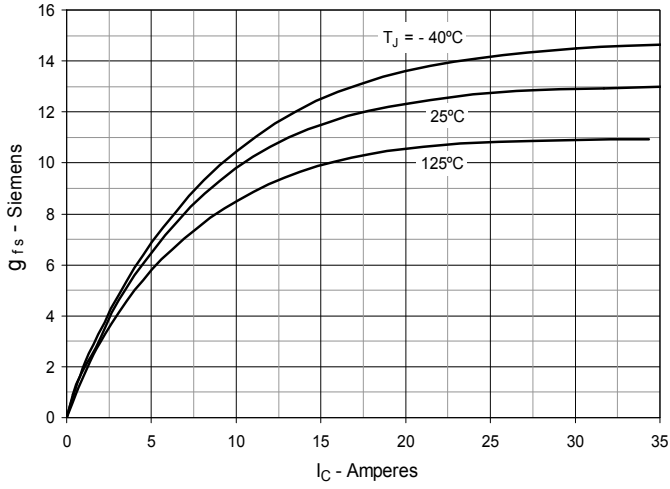


Fig. 8. Gate Charge

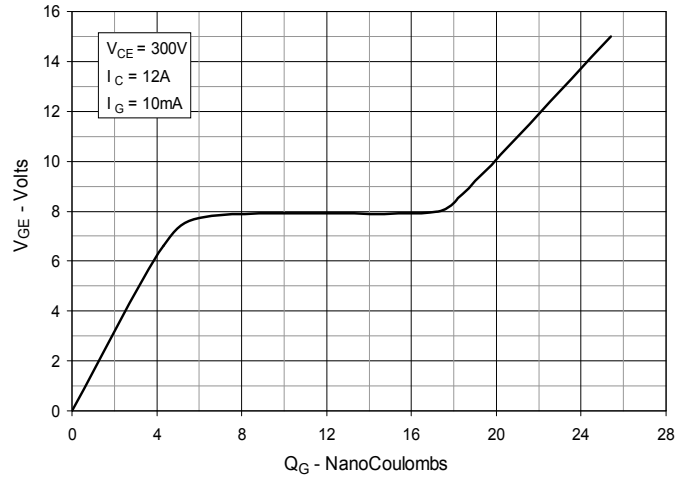


Fig. 9. Capacitance

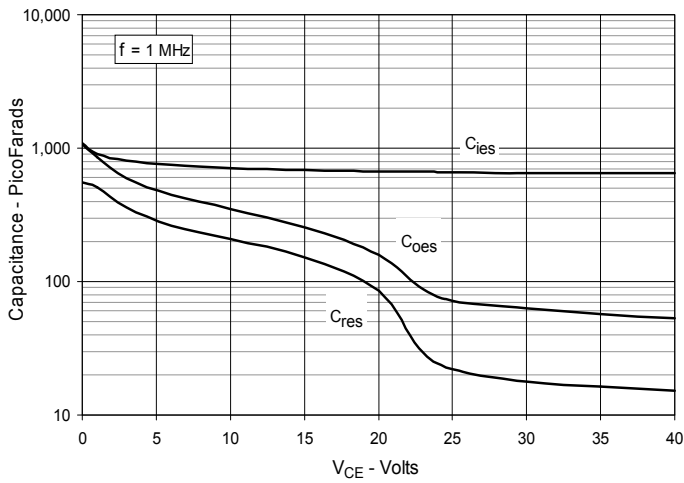


Fig. 10. Reverse-Bias Safe Operating Area

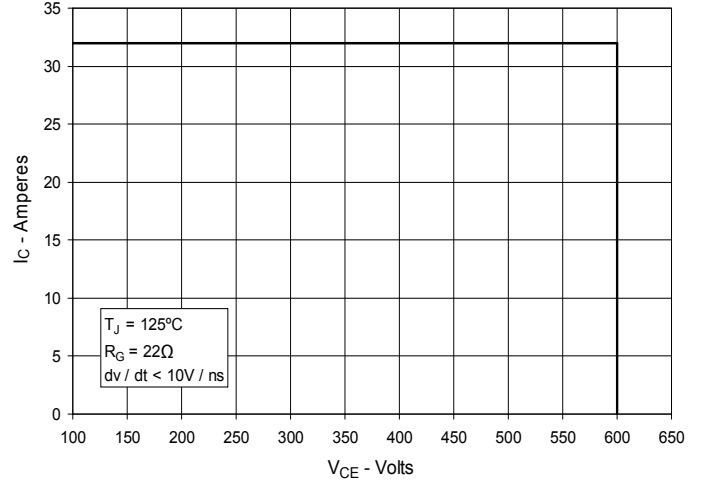


Fig. 11. Maximum Transient Thermal Impedance

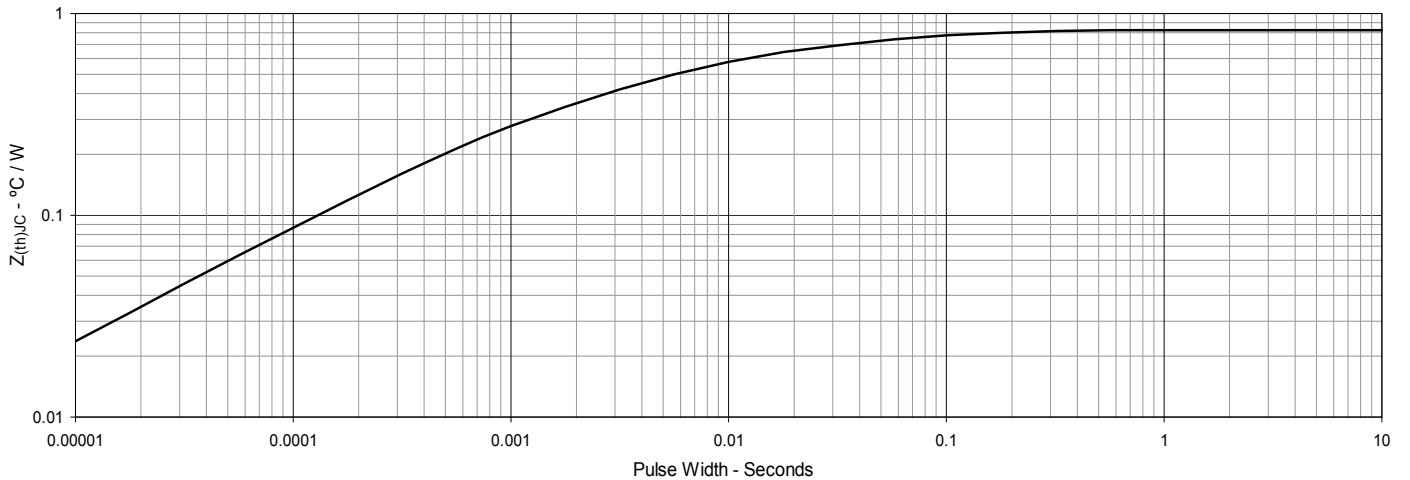


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

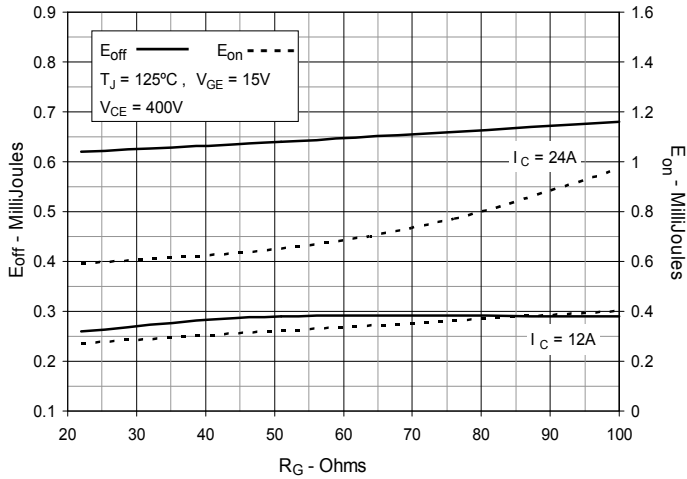


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

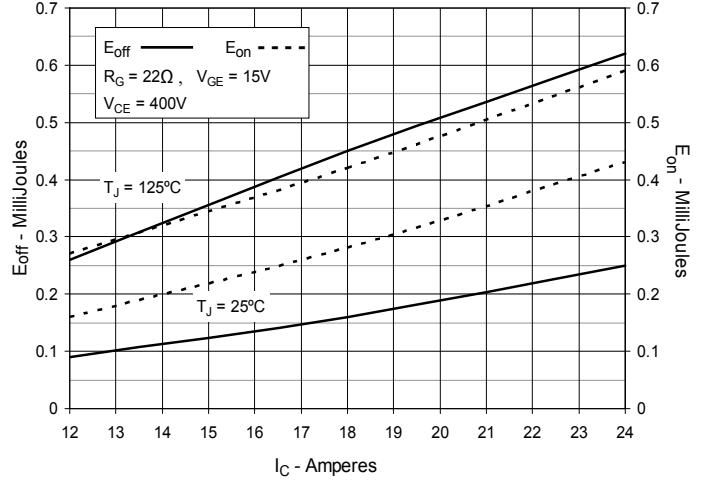


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

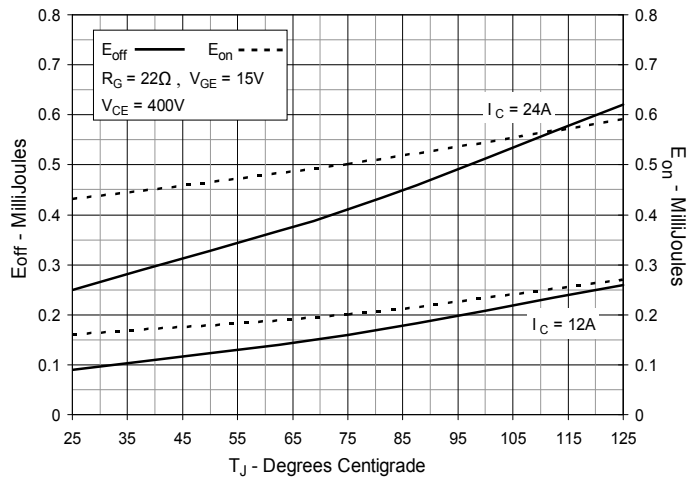


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

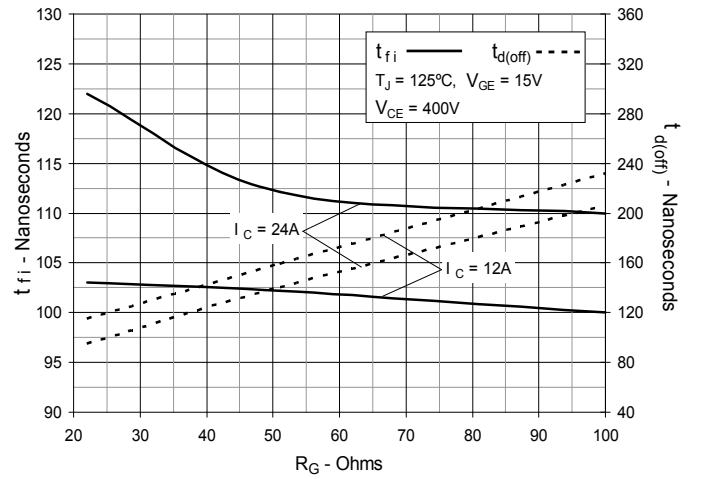


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

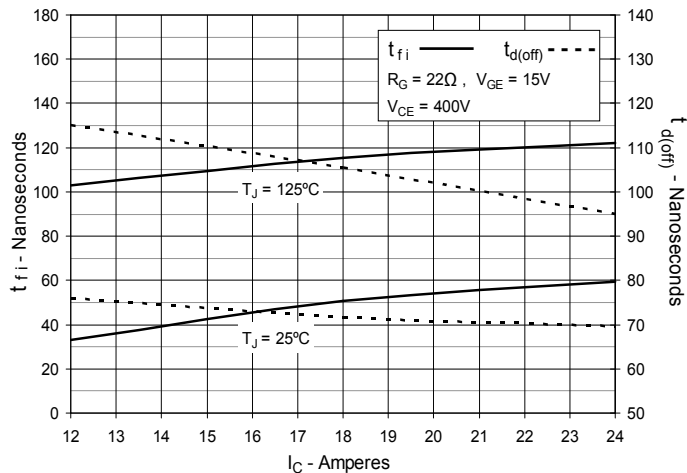


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

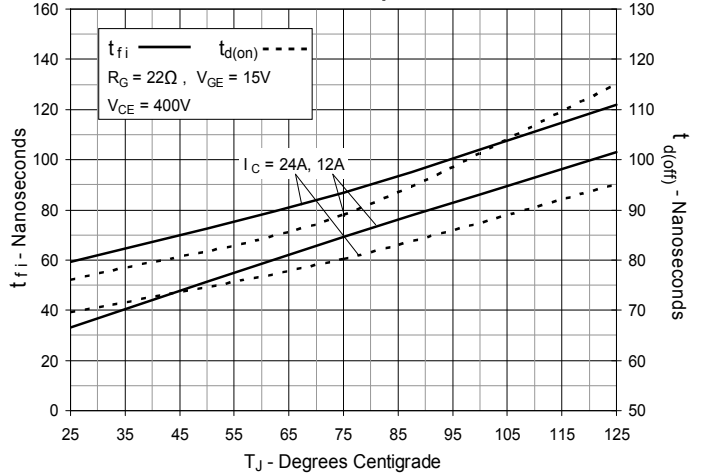


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

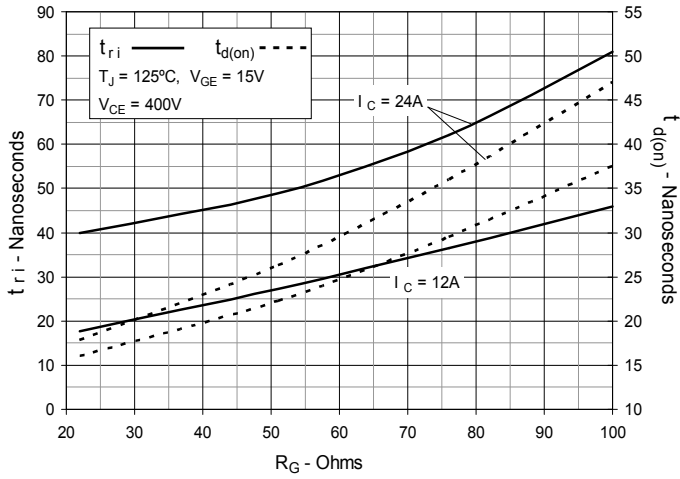


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

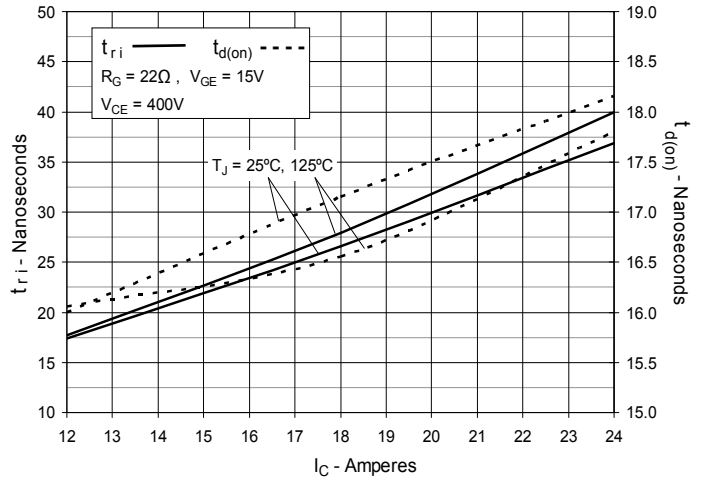


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

